

isc Silicon NPN Power Transistor

2SD1941

**DESCRIPTION**

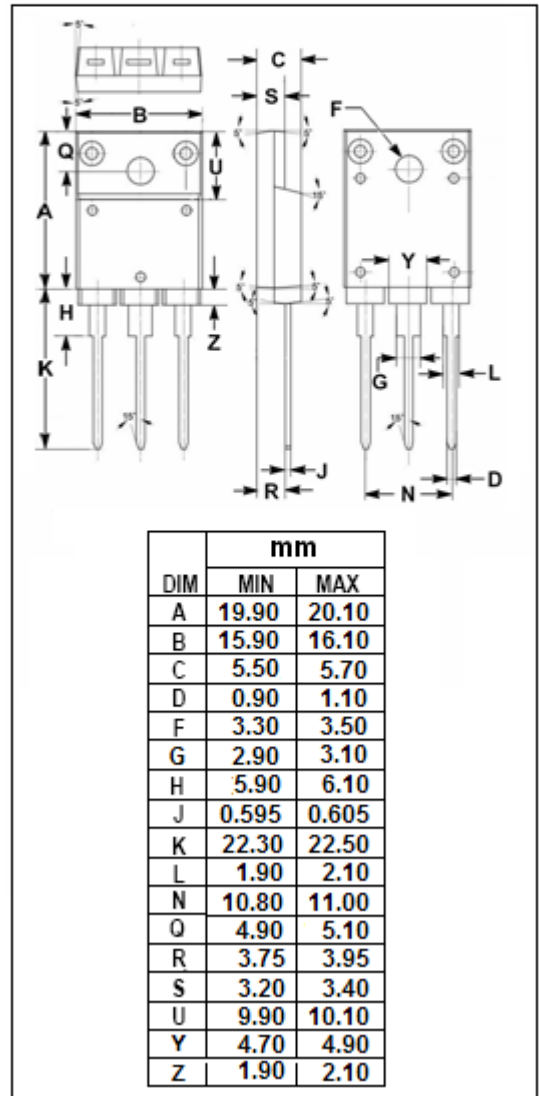
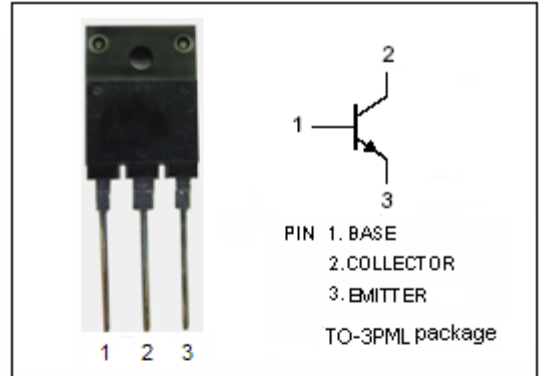
- High Breakdown Voltage-  
:  $V_{CBO} = 1500V$  (Min)
- High Switching Speed

**APPLICATIONS**

- Designed for CTV/character display horizontal deflection output stage applications

**ABSOLUTE MAXIMUM RATINGS(Ta=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	600	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current- Continuous	6	A
$I_{C(peak)}$	Collector Current- Peak	7	A
$I_{C(surge)}$	Collector Current-Surge	16	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ C$	50	W
$T_J$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature Range	-55~150	°C



**isc Silicon NPN Power Transistor****2SD1941****ELECTRICAL CHARACTERISTICS**T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; R <sub>BE</sub> = ∞	600			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10mA; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			5.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.5	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1500V; R <sub>BE</sub> = 0			500	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	5			